6080K/M

60V N-channel enhancement mode MOSFET

- **N-Channel:60V 80A**
- **RDS(on)Typ= 6.5 mΩ@VGS = 10V**

试用水印 试用水印 试用水印

General Description

This Power MOSFET is produced using Maple semi's advanced TRENCH technology.

This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Application

- PWM Application
- Load Switch
- Power Management

Package



Marking and pin assignment

试用水印 试用水印 试用水印

Absolute Maximum Ratings (TJ=25℃ unless otherwise specified)

Symbol	Parameter	SLD80N06T	Units
VDSS	Drain-Source Voltage	60	V
ID	Drain Current - Continuous (TC = 25℃)	80	A
	- Continuous (TC = 100℃)	50	A
IDM	Drain Current - Pulsed (Note 1)	320	A
VGSS	Gate-Source Voltage	±20	V
EAS	Single Pulsed Avalanche Energy	284	mJ
PD	Power Dissipation (TC = 25℃)	108	W
R θJC	Thermal Resistance, Junction to Case	1.4	℃/W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +150	℃
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	℃

* Drain current limited by maximum junction temperature.

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